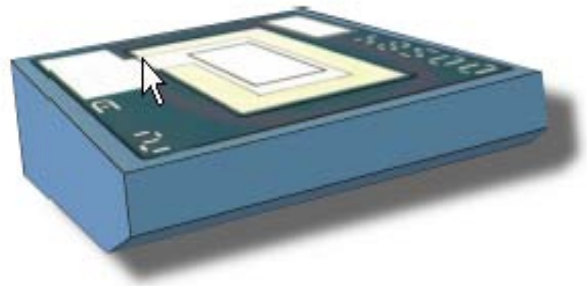


PDCS200E-LE

Side Illuminated Low Entry Monitor Photodiode

PDCS200E-LE is a side illuminated monitor photodiode chip that has an angled side facet and a large optical area for monitoring the optical output emitted from the backside of edge-emitting lasers that are mounted p-side down.



This low entry, side illuminated monitor photodiode is optimized for monitoring FP or DFB lasers used in single-mode data- and telecom applications as well as EDFA pump lasers. The monitor diode offers excellent responsivity in the wavelength region from 980 to 1620nm.

FEATURES

- Side-illuminated
- Angled side facet
- Optimized for monitoring FP or DFB lasers
- Top side anode pad

BENEFITS

- Side illuminated, low entry InGaAs monitor photodiode, without the need for a “wrap-around” submount
- Angled side facet for high coupling efficiency
- Large active area: 180 x 220 μm
- Low bias voltage: 1.5 V
- Operating temperature

APPLICATIONS

- Back facet laser monitoring

The incoming laser light, emitted from a p-down mounted edge-emitting laser, is refracted by the angled side facet onto the active area, thus producing a photocurrent proportional to the light emitted at the laser backside. Thanks to this unique side facet, a bulky and expensive “wraparound” submount is not required.

The topside anode pad is optimized for wire-bonding, whereas the cathode pad on the bottom can either be soldered or glued using conductive epoxy. As an option, the cathode on the bottom is available with a deposited layer of AuSn solder.

CHARACTERISTICS (T = 25 °C)

Parameter	Sym	U _R	Min	Typ	Max	Unit
Responsivity $\lambda = 1260 - 1620 \text{ nm}$	R	2.5V	0.3		0.6	A/W
Dark current T = 25 °C T = 85 °C	I _D	5V		10	50 500	nA
Total capacitance	C	5V	2		4	pF
Linearity	Lin	5V	-10		10	%

DIMENSIONS

Parameter	Min	Typ	Max	Unit
Chip length	300	320	330	μm
Chip width	390	400	410	μm
Chip thickness	90	100	110	μm
Light-entry facet angle	24	27	30	μm

For more information
visit www.enablence.com